

RD74LVC14B

Hex Schmitt-trigger Inverters

REJ03D0218-0100Z Rev.1.00 Apr.09.2004

Description

The RD74LVC14B has six Schmitt trigger inverters in a 14-pin package. Low voltage and high-speed operation is suitable at the battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

Features

- $V_{CC} = 2.0 \text{ V to } 5.5 \text{ V}$
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current ± 4 mA (@V_{CC} = 1.65 V) ± 8 mA (@V_{CC} = 2.3 V) ± 12 mA (@V_{CC} = 2.7 V) ± 24 mA (@V_{CC} = 3.0 V to 5.5 V)
- Ordering Information

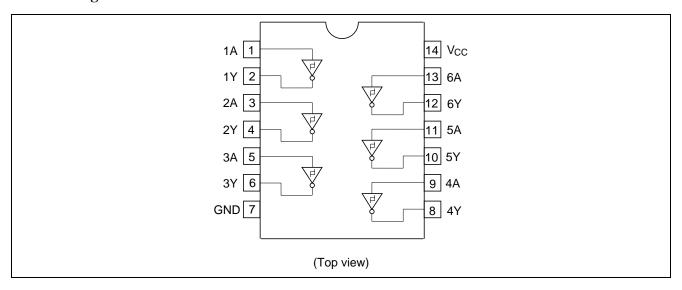
Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
RD74LVC14BFPEL	SOP-14 pin (JEITA)	FP-14DAV	FP	EL (2,000 pcs/reel)
RD74LVC14BTELL	TSSOP-14 pin	TTP-14DV	Т	ELL (2,000 pcs/reel)

Function Table

Input A	Output Y
L	Н
Н	L

H: High level L: Low level

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	Vcc	-0.5 to 7.0	V	
Input diode current	l _{IK}	- 50	mA	$V_1 = -0.5 \text{ V}$
Input voltage	Vı	-0.5 to 7.0	V	
Output diode current	Іок	- 50	mA	$V_0 = -0.5 \text{ V}$
		50		$V_O = V_{CC} + 0.5 V$
Output voltage	Vo	-0.5 to V _{CC} +0.5	V	
Output current	lo	±50	mA	
V _{CC} , GND current / pin	I _{CC} or I _{GND}	100	mA	
Storage temperature	Tstg	-65 to +150	°C	

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	Vcc	1.5 to 5.5	V	Data hold
		1.65 to 5.5		At operation
Input / Output voltage	Vı	0 to 5.5	V	A
	Vo	0 to V _{CC}		Υ
Operating temperature	Та	-40 to 85	°C	
Output current	Іон		mA	V _{CC} = 1.65 V
		- 8		$V_{CC} = 2.3 \text{ V}$
		- 12		$V_{CC} = 2.7 \text{ V}$
		-24		$V_{CC} = 3.0 \text{ V to } 5.5 \text{ V}$
	I _{OL}	4	mA	V _{CC} = 1.65 V
		8		V _{CC} = 2.3 V
		12		$V_{CC} = 2.7 \text{ V}$
		24		$V_{CC} = 3.0 \text{ V to } 5.5 \text{ V}$

Electrical Characteristics

			Ta = −40 to 85°C			
Item	Symbol	V _{cc} (V)	Min	Max	Unit	Test Conditions
Threshould voltage	V _T ⁺	1.65	0.4	1.3	V	
		1.95	0.6	1.5		
		2.3	0.8	1.7		
		2.5	0.8	1.7		
		2.7	1.0	2.0		
		3.0	1.2	2.2		
		3.6	1.5	2.4		
		4.5	1.6	2.6		
		5.5	2.0	3.0		
	V_T^-	1.65	0.15	0.85	V	
		1.95	0.25	0.95		
		2.3	0.4	1.2		
		2.5	0.4	1.2		
		2.7	0.4	1.4		
		3.0	0.6	1.5		
		3.6	0.8	1.8		
		4.5	1.0	2.0		
		5.5	1.4	2.4		
Hysteresis voltage	ΔV_{T}	1.65	0.10	1.15	V	$V_T^+ - V_T^-$
		1.95	0.15	1.25		
		2.3	0.25	1.3		
		2.5	0.25	1.3		
		2.7	0.3	1.1		
		3.0	0.4	1.2		
		3.6	0.4	1.2		
		4.5	0.4	1.2		
		5.5	0.4	1.2		
Input voltage	V_{OH}	1.65 to 5.5	V _{CC} -0.2	_	V	$I_{OH} = -100 \mu A$
		1.65	1.2	_		$I_{OH} = -4 \text{ mA}$
		2.3	1.7	_		$I_{OH} = -8 \text{ mA}$
		2.7	2.2	_		$I_{OH} = -12 \text{ mA}$
		3.0	2.4	_		
		3.0	2.2	_		$I_{OH} = -24 \text{ mA}$
		4.5	3.8	_		
	V_{OL}	1.65 to 5.5	_	0.2	V	$I_{OL} = 100 \mu A$
		1.65	_	0.45		$I_{OL} = 4 \text{ mA}$
		2.3	_	0.7		$I_{OL} = 8 \text{ mA}$
		2.7	_	0.4		I_{OL} = 12 mA
		3.0	_	0.55		$I_{OL} = 24 \text{ mA}$
_		4.5	_	0.55		
Input current	I _{IN}	0 to 5.5	_	±5.0	μA	$V_{IN} = 5.5 \text{ V or GND}$
Quiescent supply	I _{CC}	2.7 to 3.6	_	±5.0	μΑ	$V_{IN} = 3.6 \text{ V to } 5.5 \text{ V}$
current		2.7 to 5.5	_	5.0		$V_{IN} = V_{CC}$ or GND
	ΔI_{CC}	2.7 to 3.6	_	500	μΑ	V_{IN} = one input at
						$(V_{CC}-0.6)V$,
						other inputs at V _{CC} or GND

Switching Characteristics

			T	Ta = -40 to 85°C			From	То
Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	(Input)	(Output)
Propagation delay time	t _{PLH}	1.8±0.15	1.0	_	11.0	ns	Α	Υ
	t_{PHL}	2.5±0.2	1.0	_	7.8			
		2.7	1.0	_	7.5			
		3.3±0.3	1.0	_	6.4			
		5.0±0.5	1.0	_	6.0			
Between output pins skew*1	t _{OSLH}	1.8±0.15	_	_	_	ns		
	t_{OSHL}	2.5±0.2	_	_	_			
		2.7	_	_	_			
		3.3±0.3	_	_	1.0	_		
		5.0±0.5	_	_	1.0			
Input capacitance	C _{IN}	3.3	_	5.0	_	pF		

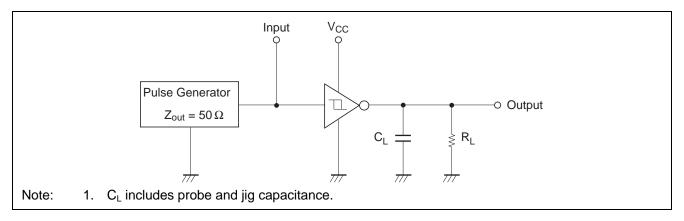
Note: 1. This parameter is characterized but not tested.

 $t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|$

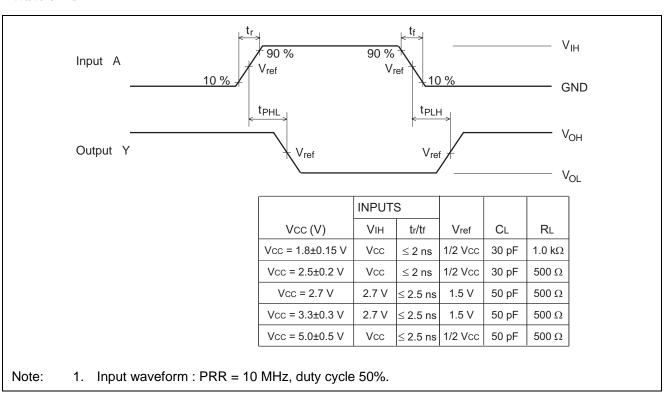
Operating Characteristics

			Ta = 25°C				
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	Test conditions
Power dissipation	C_{PD}	1.8	_	16	_	pF	f = 10 MHz
Capacitance		2.5	_	18	_	_	
		3.3	_	20	_	_	
		5.0	_	25	_	_	

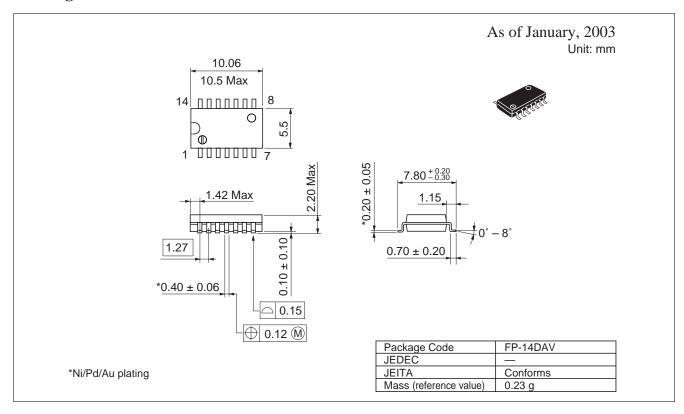
Test Circuit

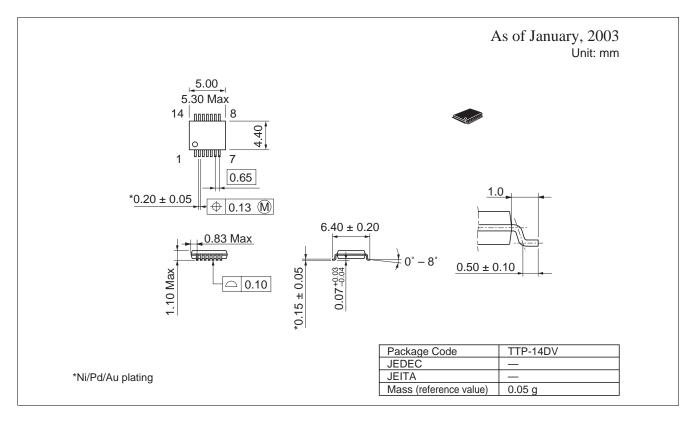


Waveforms



Package Dimensions





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Renesas Technology Europe Limited.

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, United Kingdom Tel: <44> (1628) 585 100, Fax: <44> (1628) 585 900

Renesas Technology Europe GmbHDornacher Str. 3, D-85622 Feldkirchen, Germany
Tel: <49> (89) 380 70 0, Fax: <49> (89) 929 30 11

Renesas Technology Hong Kong Ltd. 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2375-6836

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Renesas Technology (Shanghai) Co., Ltd. 26/F., Ruijin Building, No.205 Maoming Road (S), Shanghai 200020, China Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.
1, Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

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